

# Comments and Corrections

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## Corrections to “High Power X-band Monolithic GaAs PIN Balanced Limiter”

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In the footnote in page 1 of the original paper [1], the affiliation of Gary J. Cheng was not correct.

“Gary J. Cheng is with the Institute of Technological Sciences, Wuhan University, Wuhan 430072, China (e-mail: gjcheng@purdue.edu).”

Should be changed to “Gary J. Cheng is with School of Industrial Engineering, Purdue University, West Lafayette, IN USA (e-mail: gjcheng@purdue.edu).”

### REFERENCE

- [1] S. Li et al., “High power X-band monolithic GaAs PIN balanced limiter,” *IEEE Trans. Power Electron.*, vol. 38, no. 4, pp. 4623–4631, Apr. 2023, doi: [10.1109/TPEL.2022.3232612](https://doi.org/10.1109/TPEL.2022.3232612).

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